

Silicon PNP Power Transistors

2SB1186A

DESCRIPTION

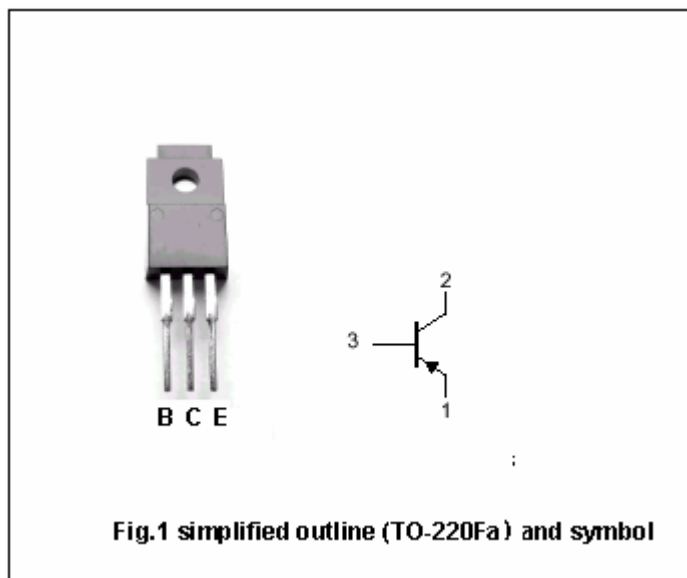
- With TO-220Fa package
- Low collector saturation voltage
- Complement to type 2SD1763A
- High breakdown voltage

APPLICATIONS

- For use in low frequency power amplifier applications

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector
3	Base

**Absolute maximum ratings(Ta=25□)**

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	-160	V
V _{CEO}	Collector -emitter voltage	Open base	-160	V
V _{EBO}	Emitter-base voltage	Open collector	-5	V
I _C	Collector current		-1.5	A
I _{CM}	Collector current-peak		-3.0	A
P _C	Collector power dissipation	T _a =25□	2.0	W
		T _C =25□	20	
T _j	Junction temperature		150	□
T _{stg}	Storage temperature		-55~150	□

Silicon PNP Power Transistors

2SB1186A

CHARACTERISTICS

T_j=25 °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =-1mA; I _B =0	-160			V
V _{(BR)CBO}	Collector-base breakdown voltage	I _C =-50μA; I _E =0	-160			V
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =-50μA; I _C =0	-5			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =-1A; I _B =-0.1A			-2.0	V
V _{BEsat}	Base-emitter saturation voltage	I _C =-1A; I _B =-0.1A			-1.5	V
I _{CBO}	Collector cut-off current	V _{CB} =-120V; I _E =0			-1.0	μA
I _{EBO}	Emitter cut-off current	V _{EB} =-4V; I _C =0			-1.0	μA
h _{FE}	DC current gain	I _C =-0.1A; V _{CE} =-5V	60		200	
f _T	Transition frequency	I _C =-0.1A; V _{CE} =-5V		50		MHz
C _{OB}	Collector output capacitance	I _E =0; f=1MHz; V _{CB} =-10V		30		pF

◆ h_{FE} Classifications

D	E
60-120	100-200

Silicon PNP Power Transistors

2SB1186A

PACKAGE OUTLINE

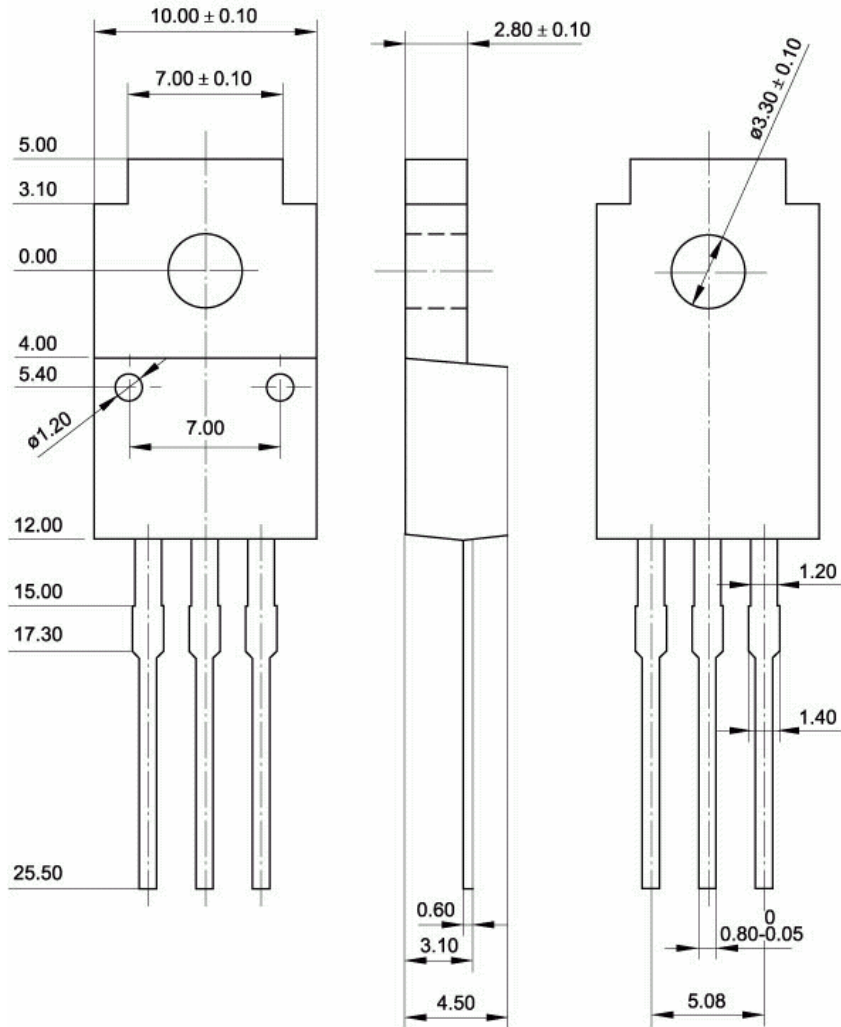


Fig.2 Outline dimensions (unindicated tolerance: ± 0.15 mm)